



Vincotech

10-EY126PA100M7-L198F78T

datasheet

flowPACK E2

1200 V / 100 A

Topology features

- Inverter
- Open Emitter configuration
- Temperature sensor

Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current
- Switching optimized for EMC

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

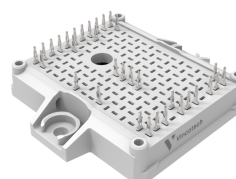
Target applications

- Industrial Drives
- UPS

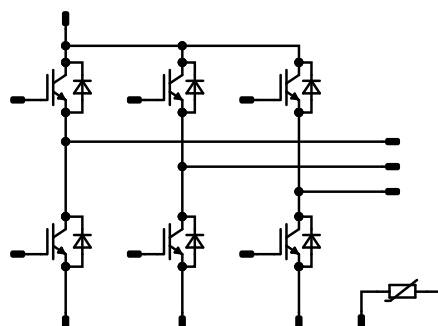
Types

- 10-EY126PA100M7-L198F78T

flow E2 12 mm housing



Schematic





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Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	92	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	200	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	174	W
Gate-emitter voltage	V_{GES}		± 20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$, $V_{CC} = 800\text{ V}$ $T_j = 150\text{ °C}$	9,5	μs
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Inverter Diode

Peak repetitive reverse voltage	V_{RRM}		1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	70	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	200	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	121	W
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	$^{\circ}\text{C}$
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	$^{\circ}\text{C}$

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Isolation voltage	V_{isol}	AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			>12,7	mm
Clearance			9,08	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,01	25	5,4	6	6,6	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		100	25 125 150		1,61 1,82 1,91	1,85 ⁽¹⁾	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			100	µA
Gate-emitter leakage current	I_{GES}		20	0		25			200	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	0	10		25			21000		pF
Output capacitance	C_{oes}							700		pF
Reverse transfer capacitance	C_{res}							280		pF
Gate charge	Q_g	$V_{CC} = 600$ V	0/15		100	25		700		nC

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						0,55		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 2$ Ω $R_{goff} = 2$ Ω	±15	600	100	25 125 150		118,2 118,2 117,6		ns
Rise time	t_r					25 125 150		10,2 12,4 13,4		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		173,6 200,4 205,6		ns
Fall time	t_f					25 125 150		82,85 96,38 106,77		ns
Turn-on energy (per pulse)	E_{on}					25 125 150		3,26 4,87 5,37		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		6,6 8,77 9,49		mWs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Diode

Static

Forward voltage	V_F				100	25 125 150		1,82 1,96 1,97	2,1 ⁽¹⁾	V
Reverse leakage current	I_R	$V_i = 1200$ V				25			40	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						0,79		K/W
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Dynamic

Peak recovery current	I_{RM}	$di/dt=9387$ A/μs $di/dt=7872$ A/μs $di/dt=8350$ A/μs	± 15	600	100	25 125 150		178,25 165,9 164,61		A
Reverse recovery time	t_{rr}					25 125 150		149,24 311,54 339,17		ns
Recovered charge	Q_r					25 125 150		11,6 17,27 19,18		μC
Reverse recovered energy	E_{rec}					25 125 150		5,14 7,75 8,59		mWs
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125 150		4044 2649 2147		A/μs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Thermistor

Static

Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	$R_{100} = 493 \Omega$				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 2 \%$						3375		K
B-value	$B_{(25/100)}$	Tol. $\pm 2 \%$						3437		K
Vincotech Thermistor Reference									K	

⁽¹⁾ Value at chip level

⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.



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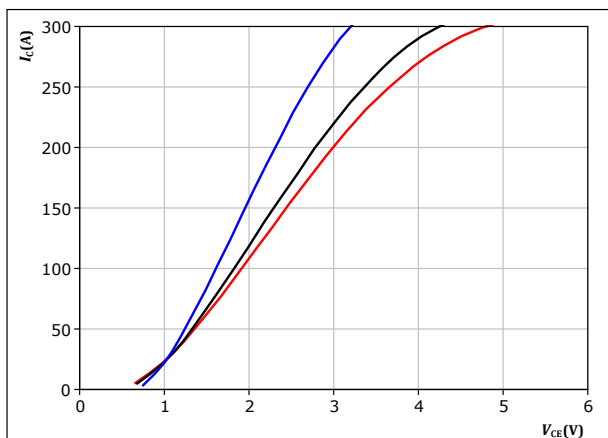
datasheet

Inverter Switch Characteristics

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

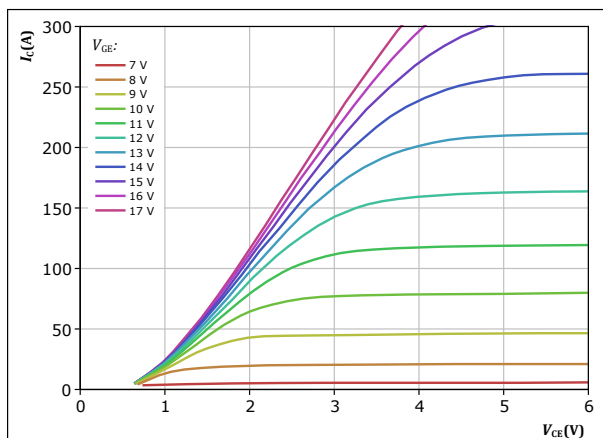


$t_p = 250 \mu s$
 $V_{GE} = 15 V$
 $T_j: 25 ^\circ C, 125 ^\circ C, 150 ^\circ C$

figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

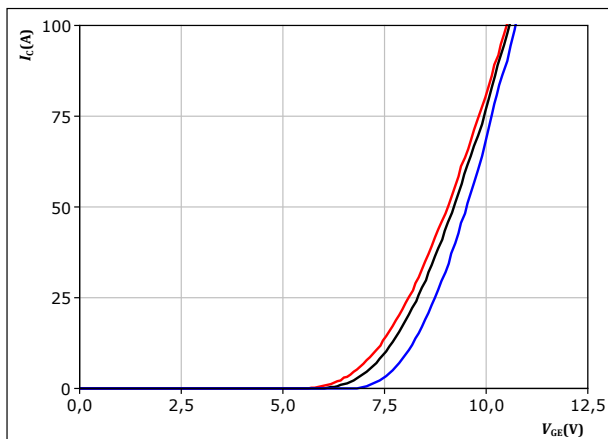


$t_p = 250 \mu s$
 $T_j = 150 ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

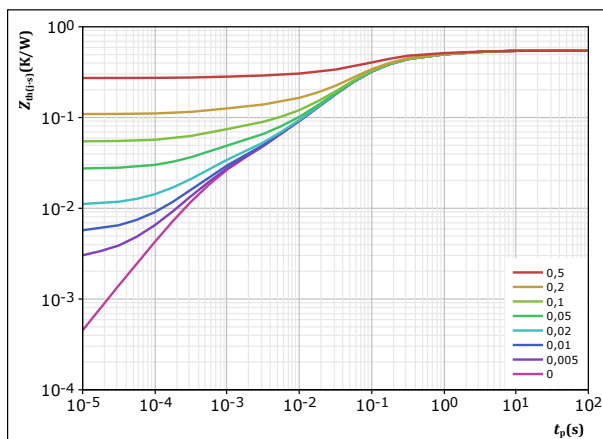


$t_p = 250 \mu s$
 $V_{CE} = 10 V$
 $T_j: 25 ^\circ C, 125 ^\circ C, 150 ^\circ C$

figure 4. IGBT

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 0,545 K/W$
IGBT thermal model values

$R (K/W)$	$\tau (s)$
5,00E-02	2,85E+00
9,49E-02	5,03E-01
2,74E-01	9,38E-02
8,25E-02	3,17E-02
2,20E-02	5,55E-03
2,13E-02	5,96E-04



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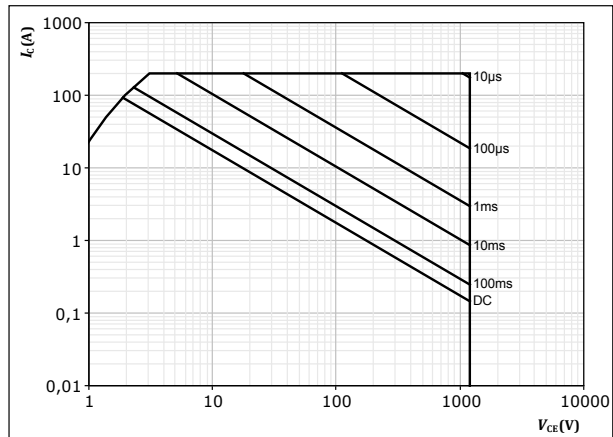
datasheet

Inverter Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$

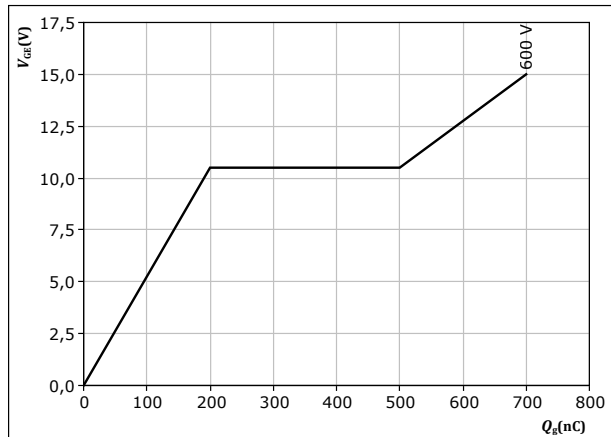


$D =$ single pulse
 $T_s = 80$ °C
 $V_{GE} = 15$ V
 $T_j = T_{jmax}$

figure 6. IGBT

Gate voltage vs gate charge

$$V_{GE} = f(Q_g)$$



$I_C = 100$ A
 $T_j = 25$ °C



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Inverter Diode Characteristics

figure 7.

FWD

Typical forward characteristics

$$I_F = f(V_F)$$

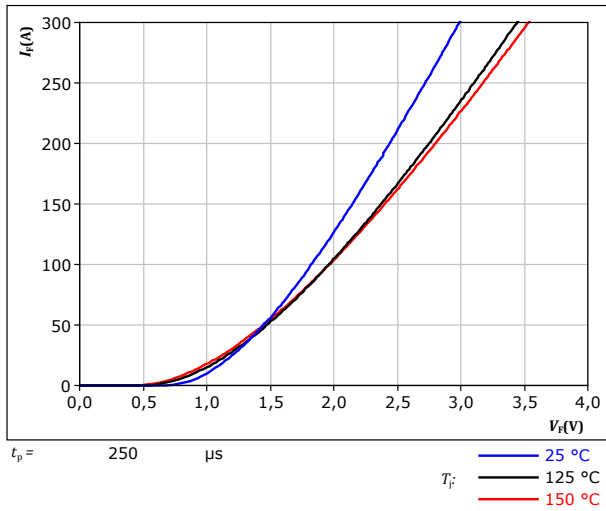
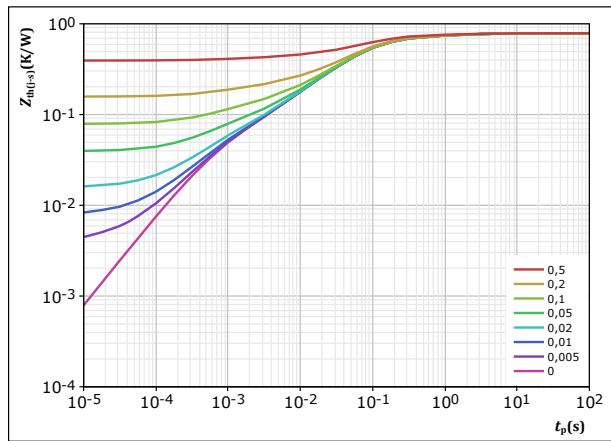


figure 8.

FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D =$	t_p / T	
$R_{th(j-s)} =$	0,787	K/W
FWD thermal model values		
R (K/W)	τ (s)	
4,05E-02	3,25E+00	
9,02E-02	5,38E-01	
3,71E-01	8,95E-02	
1,97E-01	3,04E-02	
5,23E-02	4,59E-03	
3,58E-02	6,26E-04	



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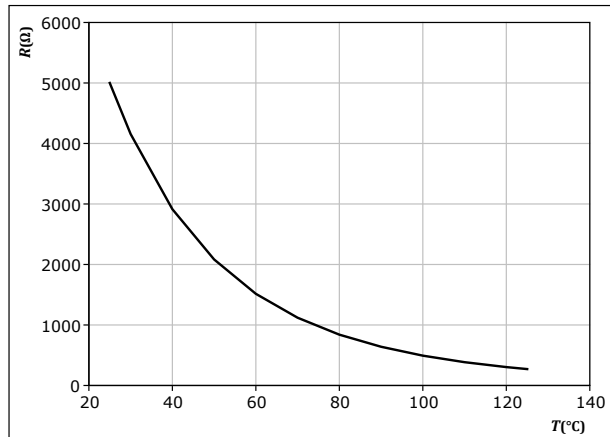
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Thermistor Characteristics

figure 9. Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$





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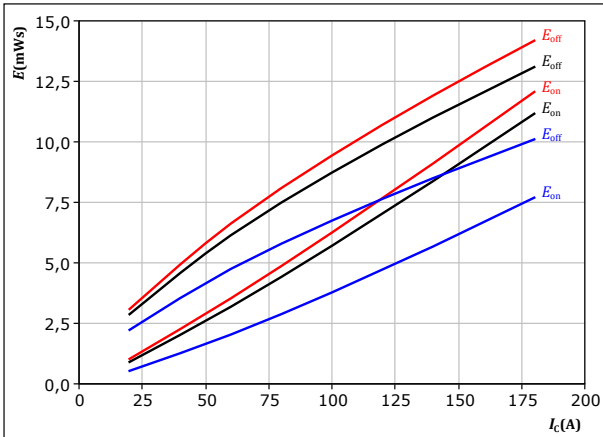
Inverter Switching Characteristics

figure 10.

IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_c)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 2 \text{ } \Omega$
 $R_{goff} = 2 \text{ } \Omega$

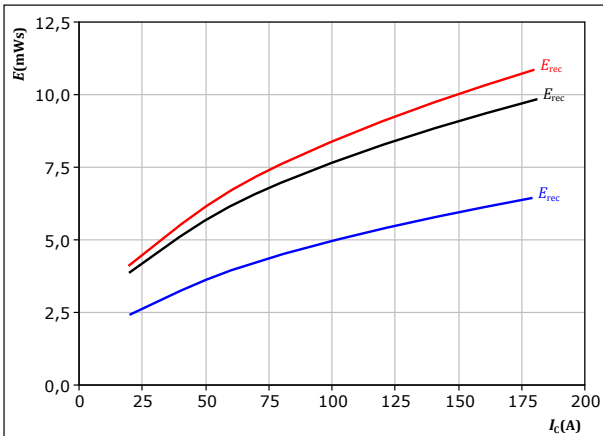
T_j : $25 \text{ } ^\circ\text{C}$ (blue)
 $125 \text{ } ^\circ\text{C}$ (black)
 $150 \text{ } ^\circ\text{C}$ (red)

figure 12.

FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{rec} = f(I_c)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 2 \text{ } \Omega$

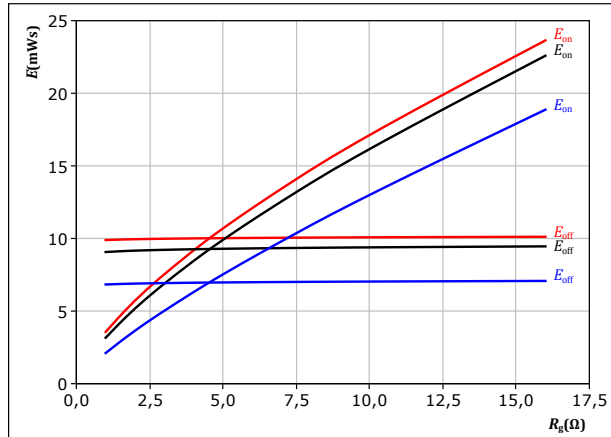
T_j : $25 \text{ } ^\circ\text{C}$ (blue)
 $125 \text{ } ^\circ\text{C}$ (black)
 $150 \text{ } ^\circ\text{C}$ (red)

figure 11.

IGBT

Typical switching energy losses as a function of IGBT turn on gate resistor

$$E = f(R_g)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 100 \text{ A}$

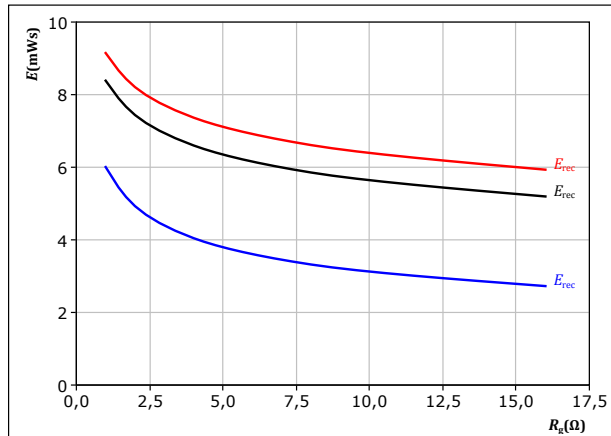
T_j : $25 \text{ } ^\circ\text{C}$ (blue)
 $125 \text{ } ^\circ\text{C}$ (black)
 $150 \text{ } ^\circ\text{C}$ (red)

figure 13.

FWD

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 100 \text{ A}$

T_j : $25 \text{ } ^\circ\text{C}$ (blue)
 $125 \text{ } ^\circ\text{C}$ (black)
 $150 \text{ } ^\circ\text{C}$ (red)



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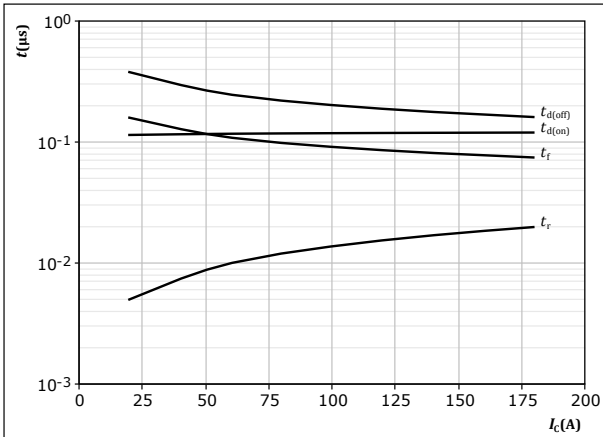
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Inverter Switching Characteristics

figure 14.

IGBT

Typical switching times as a function of collector current
 $t = f(I_c)$



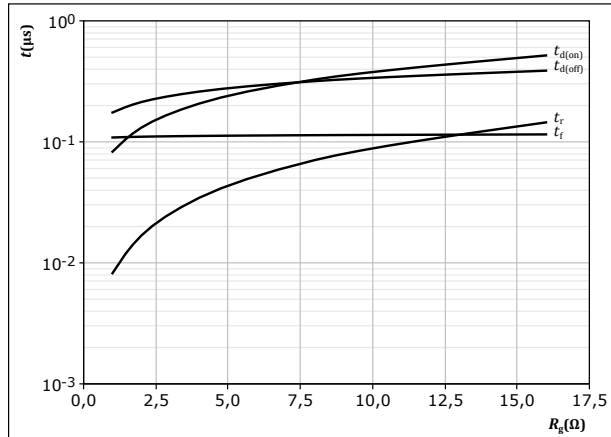
With an inductive load at

$T_j = 150$ °C
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 2$ Ω
 $R_{goff} = 2$ Ω

figure 15.

IGBT

Typical switching times as a function of IGBT turn on gate resistor
 $t = f(R_g)$



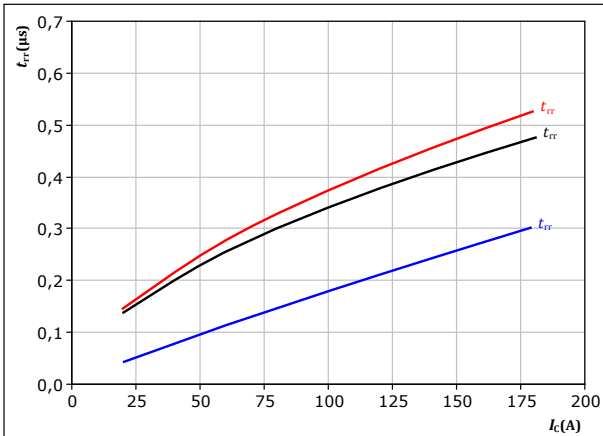
With an inductive load at

$T_j = 150$ °C
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 100$ A

figure 16.

FWD

Typical reverse recovery time as a function of collector current
 $t_{rr} = f(I_c)$



With an inductive load at

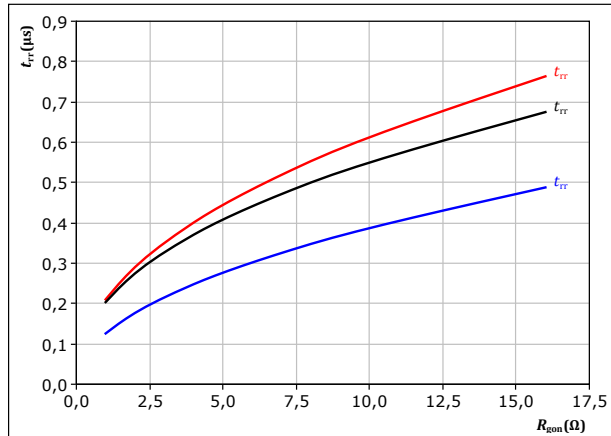
$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 2$ Ω

T_j :
— 25 °C
— 125 °C
— 150 °C

figure 17.

FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor
 $t_{rr} = f(R_{gon})$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 100$ A

T_j :
— 25 °C
— 125 °C
— 150 °C



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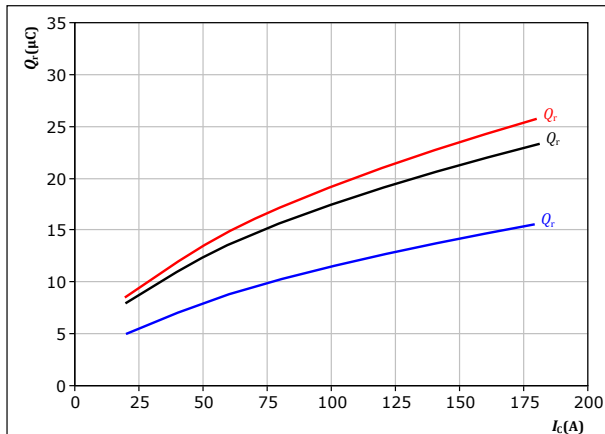
Inverter Switching Characteristics

figure 18.

FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 2$ Ω

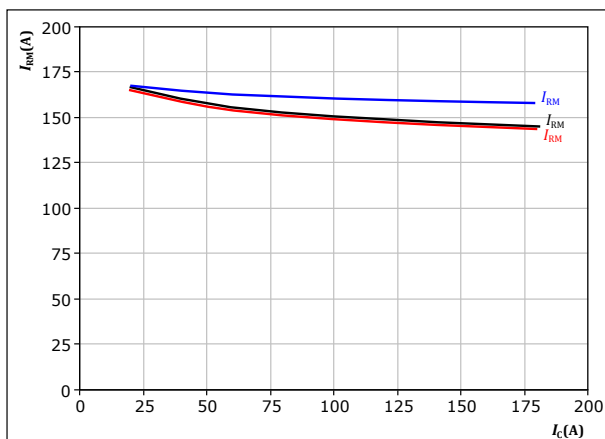
T_j : 25 °C
125 °C
150 °C

figure 20.

FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 2$ Ω

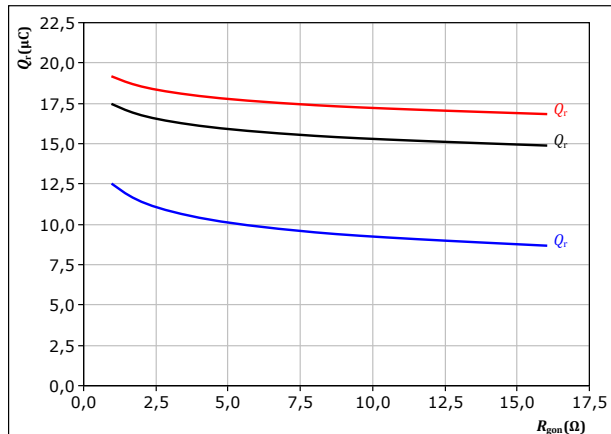
T_j : 25 °C
125 °C
150 °C

figure 19.

FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$$Q_r = f(R_{gon})$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 100$ A

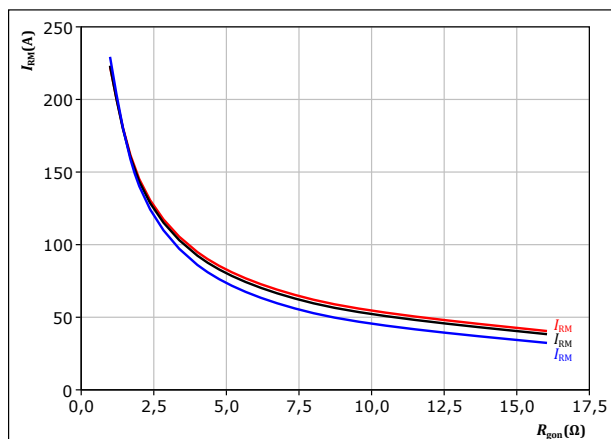
T_j : 25 °C
125 °C
150 °C

figure 21.

FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RM} = f(R_{gon})$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 100$ A

T_j : 25 °C
125 °C
150 °C



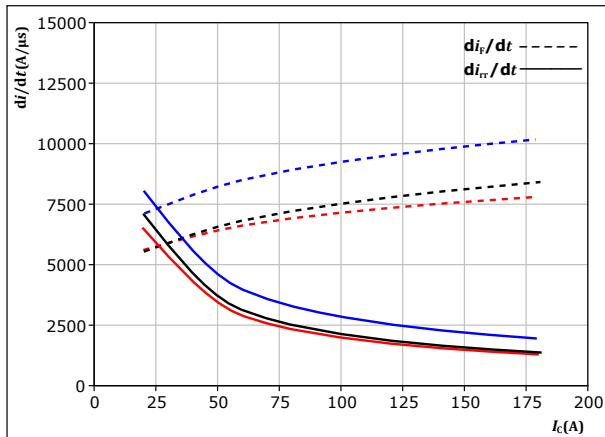
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Inverter Switching Characteristics

figure 22. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_r/dt = f(I_C)$

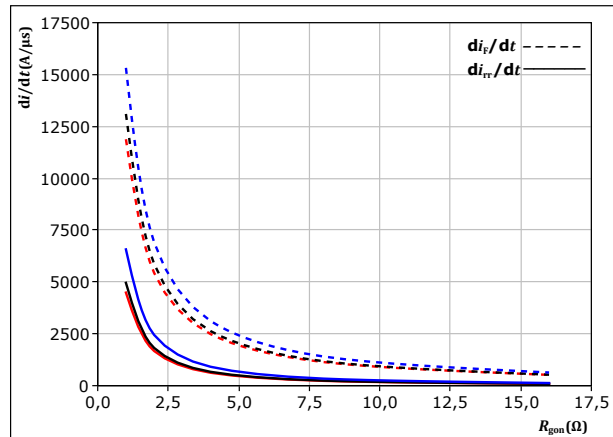


With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 2 \text{ } \Omega$
 $T_j = 25 \text{ } ^\circ\text{C}$
 $T_j = 125 \text{ } ^\circ\text{C}$
 $T_j = 150 \text{ } ^\circ\text{C}$

figure 23. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_r/dt = f(R_{gon})$



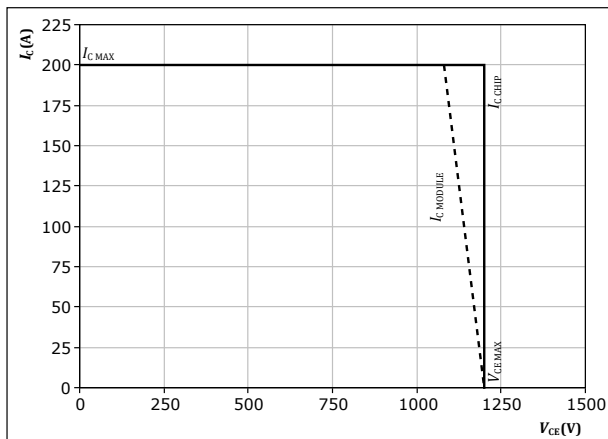
With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_C = 100 \text{ A}$
 $T_j = 25 \text{ } ^\circ\text{C}$
 $T_j = 125 \text{ } ^\circ\text{C}$
 $T_j = 150 \text{ } ^\circ\text{C}$

figure 24. IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At $T_j = 150 \text{ } ^\circ\text{C}$
 $R_{gon} = 2 \text{ } \Omega$
 $R_{goff} = 2 \text{ } \Omega$



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Inverter Switching Definitions

figure 25. IGBT

Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

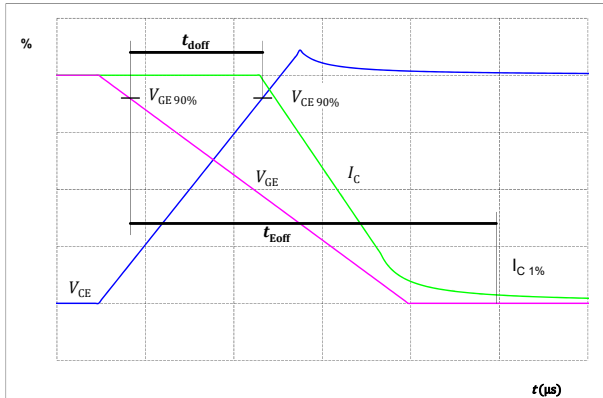


figure 26. IGBT

Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})

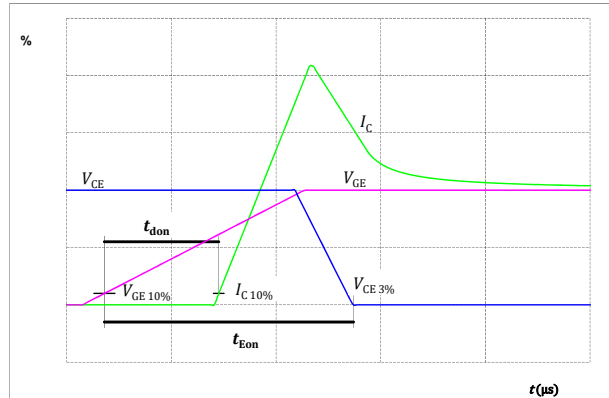


figure 27. IGBT

Turn-off Switching Waveforms & definition of t_f

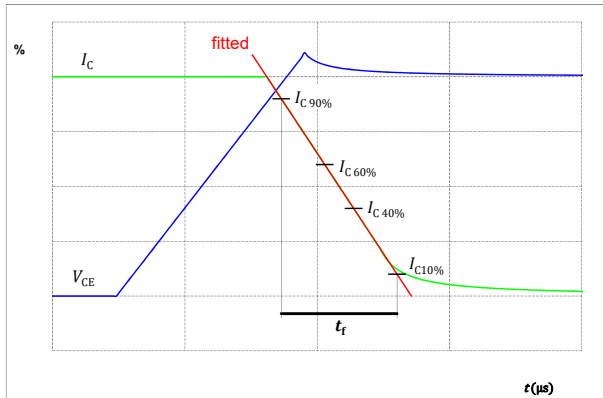
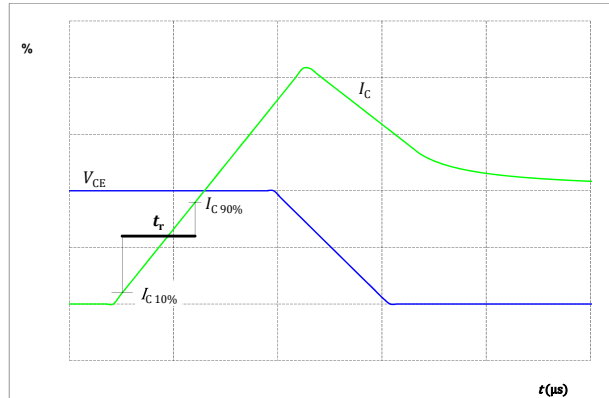


figure 28. IGBT

Turn-on Switching Waveforms & definition of t_r





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Inverter Switching Definitions

figure 29.

FWD

Turn-off Switching Waveforms & definition of t_{rr}

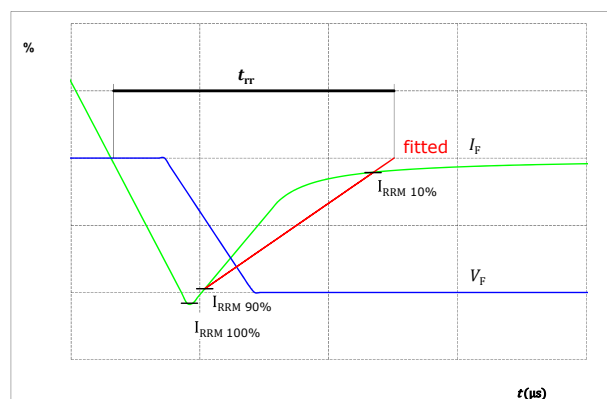
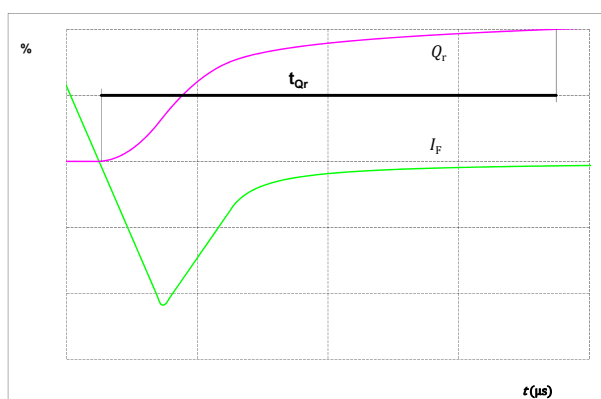


figure 30.

FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)






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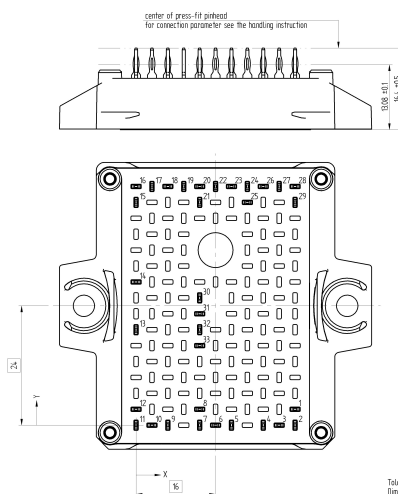
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datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-EY126PA100M7-L198F78T
With thermal paste (5,2 W/mK, PTM6000HV)	10-EY126PA100M7-L198F78T-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-EY126PA100M7-L198F78T-/3/

Marking						
	Text	Name	Date code	UL & VIN	Lot	Serial
		NN-NNNNNNNNNNNNNN- TTTTTVV	WWYY	UL VIN	LLLLL	SSSS
Datamatrix	Type&Ver	Lot number	Serial	Date code		
	TTTTTVV	LLLLL	SSSS	WWYY		

Outline				
Pin table [mm]				
Pin	X	Y	Function	
1	32	3,2	G16	
2	32	0	Ph3	
3	28,8	0	Ph3	
4	25,6	0	Ph3	
5	19,2	0	Ph2	
6	16	0	Ph2	
7	12,8	0	Ph2	
8	12,8	3,2	G14	
9	6,4	0	Ph1	
10	3,2	0	Ph1	
11	0	0	Ph1	
12	0	3,2	G12	
13	0	19,2	Therm1	
14	0	28,8	Therm2	
15	0	44,8	G11	
16	0	48	DC-1	
17	3,2	48	DC-1	
18	6,4	48	DC-1	
19	9,6	48	DC-1	
20	12,8	48	DC-2	
21	12,8	44,8	G13	
22	16	48	DC-2	
23	19,2	48	DC-2	
24	22,4	48	DC-2	
25	22,4	44,8	G15	
26	25,6	48	DC-3	
27	28,8	48	DC-3	
28	32	48	DC-3	
29	32	44,8	DC-3	
30	12,8	25,6	DC+	
31	12,8	22,4	DC+	
32	12,8	19,2	DC+	
33	12,8	16	DC+	



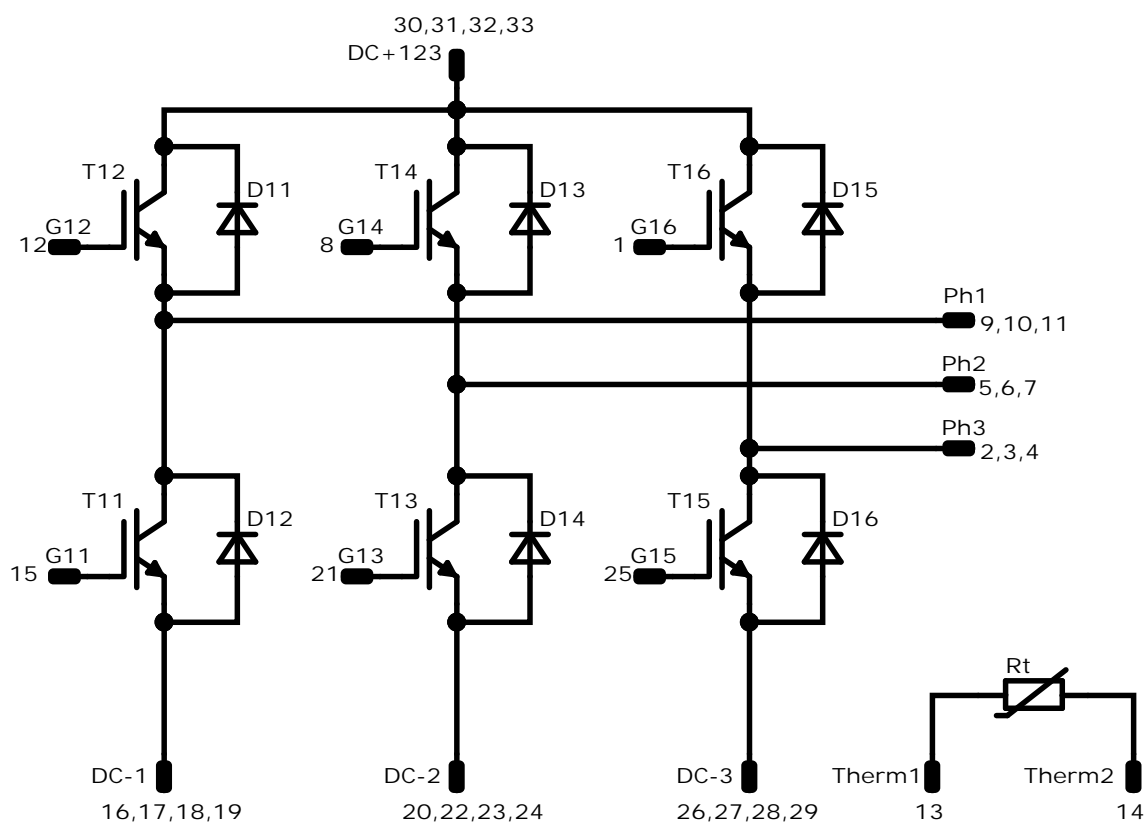
Tolerance of pinposition: +0,6mm at the end of pins
Dimension of coordinate axis is only offset without tolerance



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Pinout




Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	100 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	100 A	Inverter Diode	
Rt	NTC			Thermistor	



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Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample
Handling instruction				
Handling instructions for <i>flow</i> E2 packages see vincotech.com website.				
Package data				
Package data for <i>flow</i> E2 packages see vincotech.com website.				
Vincotech thermistor reference				
See Vincotech thermistor reference table at vincotech.com website.				
UL recognition and file number				
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.				

Document No.:	Date:	Modification:	Pages
10-EY126PA100M7-L198F78T-D6-14	30 Jun. 2023	New Datasheet format, module is unchanged Separate datasheet	

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